










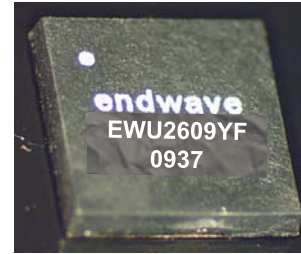


EWU2609YF

Features

-  Extremely high integration
-  Includes converter, LO doubler, RF VGA
-  IF bandwidth: 0 to 4 GHz
-  Conversion gain: +18 dB, typical at max gain
-  Output IP3: +30 dBm, typical
-  LO leakage: -5 dBm, typical
-  Low power consumption : +4.5V @ 500 mA
-  100% DC and RF tested
-  HBM Class 1A - ESD Protection Bias Circuitry
-  Package: 5 x 5 mm, 32 lead, plastic overmold QFN
-  RoHS compliant

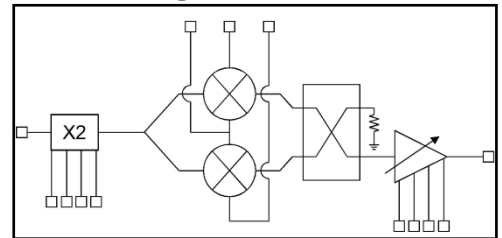
Device Photo



Description

The Endwave *EWU2609YF* is a highly integrated GaAs PHEMT MMIC upconverter that includes LO multiplication, along with RF gain adjustability via a unique voltage variable attenuator. The device provides 18 dB of conversion gain with 20 dB of RF gain adjustability, while maintaining +30 dBm output third order intercept over all conditions with 5 dBm of LO input power. This device has integrated ESD protection bias circuitry and may be used for a wide range of applications from defense electronics to commercial communication systems. All parts are 100% DC and RF tested and visually inspected per IPC-A-610.

Block Diagram

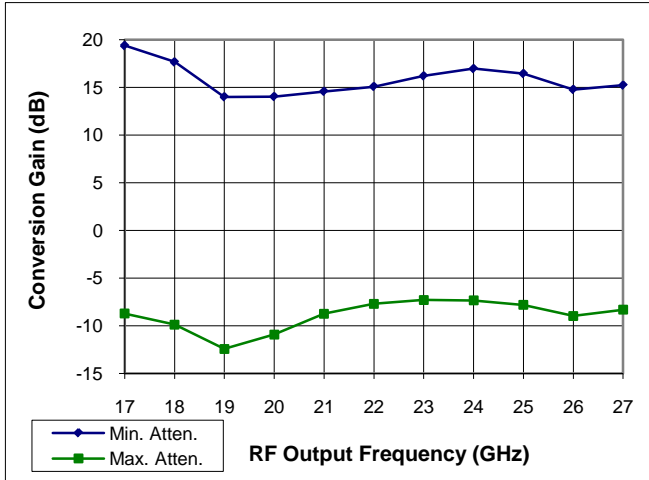


Electrical Characteristics (Temperature = +25°C)

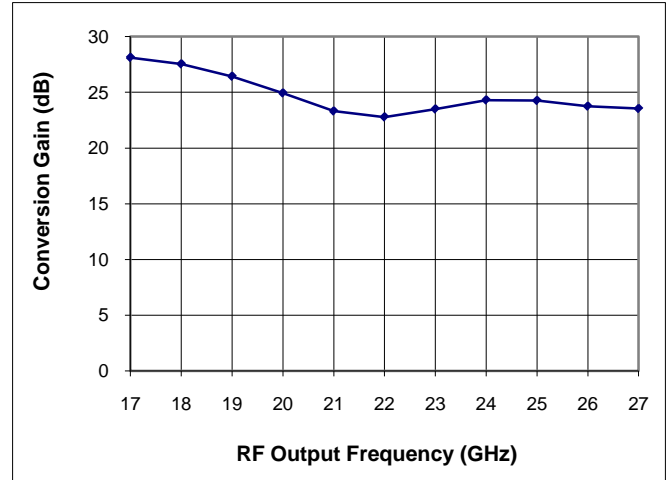
| Parameter | Min. | Typ. | Max. | Units |
|---|------|------|-------|-------|
| Frequency Range, IF | DC | | 4 | GHz |
| Frequency Range, RF | 17.7 | | 26.5 | GHz |
| Frequency Range, LO | 6.85 | | 15.25 | GHz |
| Conversion Gain (at max gain) | 15 | 18 | | dB |
| Dynamic Range ($V_{gc1,2} = 0$ vs. $-1.5V$) | | 20 | | dBm |
| LO Leakage (RF port, all gain settings) | | -5 | | dBc |
| LO Drive Power | | +5 | | dBc |
| Output 3 rd -Order Intercept (all gain settings) | | +30 | | dBm |
| Noise Figure (at maximum gain) | | 16 | | dB |
| IF Return Loss | | 10 | | dB |
| LO Return Loss | | 10 | | dB |
| RF Return Loss | | 10 | | dB |
| Drain Bias Voltages (V_{d1}, V_{d2}, V_{d3}) | | +4.5 | | V |
| Drain Bias Currents ($I_{d1}+I_{d2}+I_{d3}$) | | 500 | | mA |
| Gate Bias Voltage (V_{g3}) | | -1.2 | | V |
| Gate Bias Voltage (V_{g4}) | | -0.6 | | V |
| Gate Control Voltage ($V_{gc1,2}$) | -1.5 | | 0 | V |

EWU2609YF

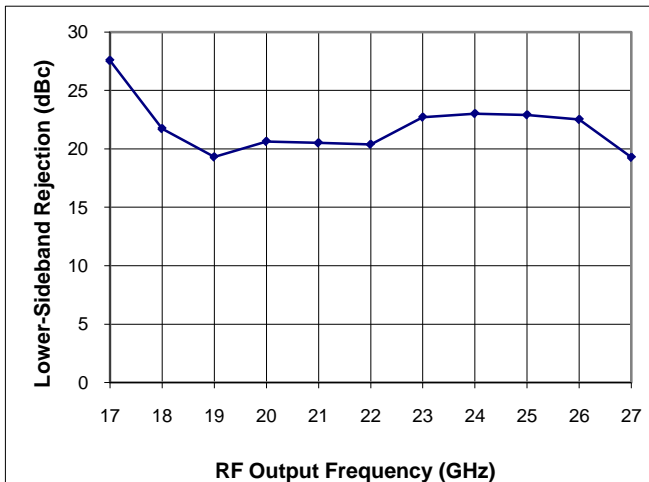
Conversion Gain
VG3=-1.2V, IF=2 GHz from external 180-degree hybrid,
 $P_{LO}=+5$ dBm at $F_{LO} = F_{RF} - F_{IF}$



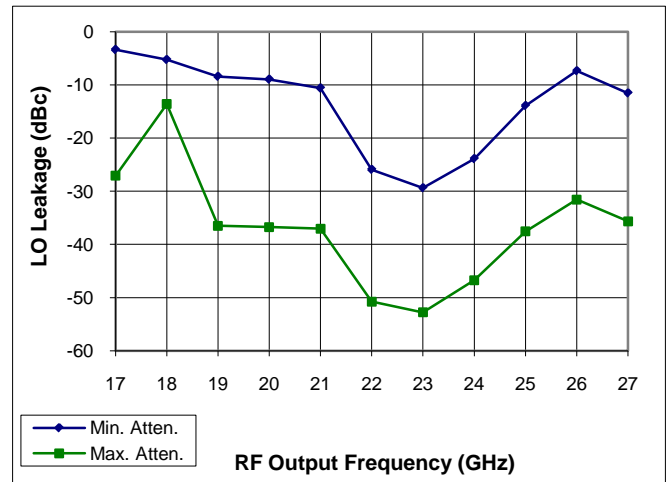
Dynamic Range
VG3=-1.2V, IF=2 GHz from external 180-degree hybrid,
 $P_{LO}=+5$ dBm at $F_{LO} = F_{RF} - F_{IF}$



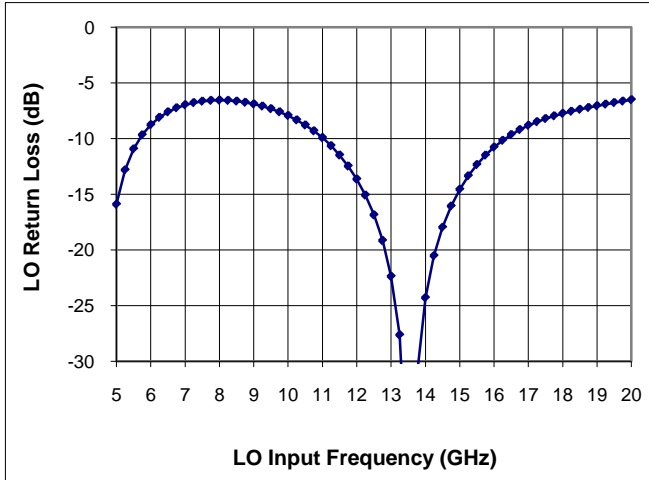
Lower-Sideband Rejection
VG3=-1.2V, IF=2 GHz from external 180-degree hybrid,
 $P_{LO}=+5$ dBm at $F_{LO} = F_{RF} - F_{IF}$



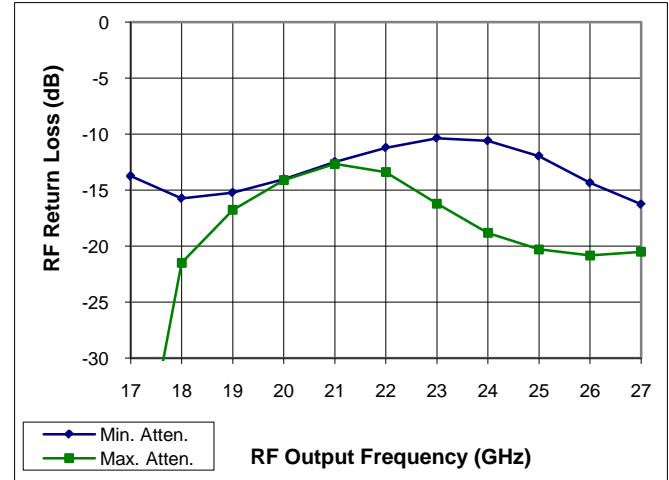
LO Leakage
VG3=-1.2V, IF=2 GHz from external 180-degree hybrid,
 $P_{LO}=+5$ dBm at $F_{LO} = F_{RF} - F_{IF}$



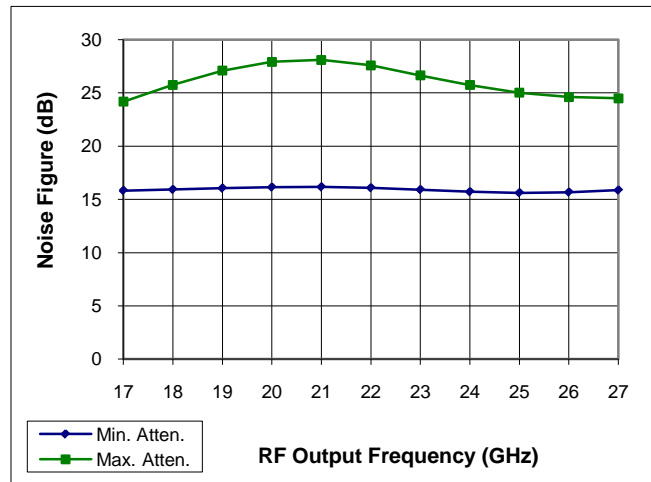
LO Return Loss
VG3=-1.2V, P_{LO}=+5 dBm



RF Return Loss
VG3=-1.2V, IF=2 GHz from external 180-degree hybrid,
P_{LO}=+5 dBm at F_{LO} = F_{RF} - F_{IF}



Noise Figure
VG3=-1.2V, IF=2 GHz from external 180-degree
hybrid, P_{LO}=+5 dBm at F_{LO} = F_{RF} - F_{IF}



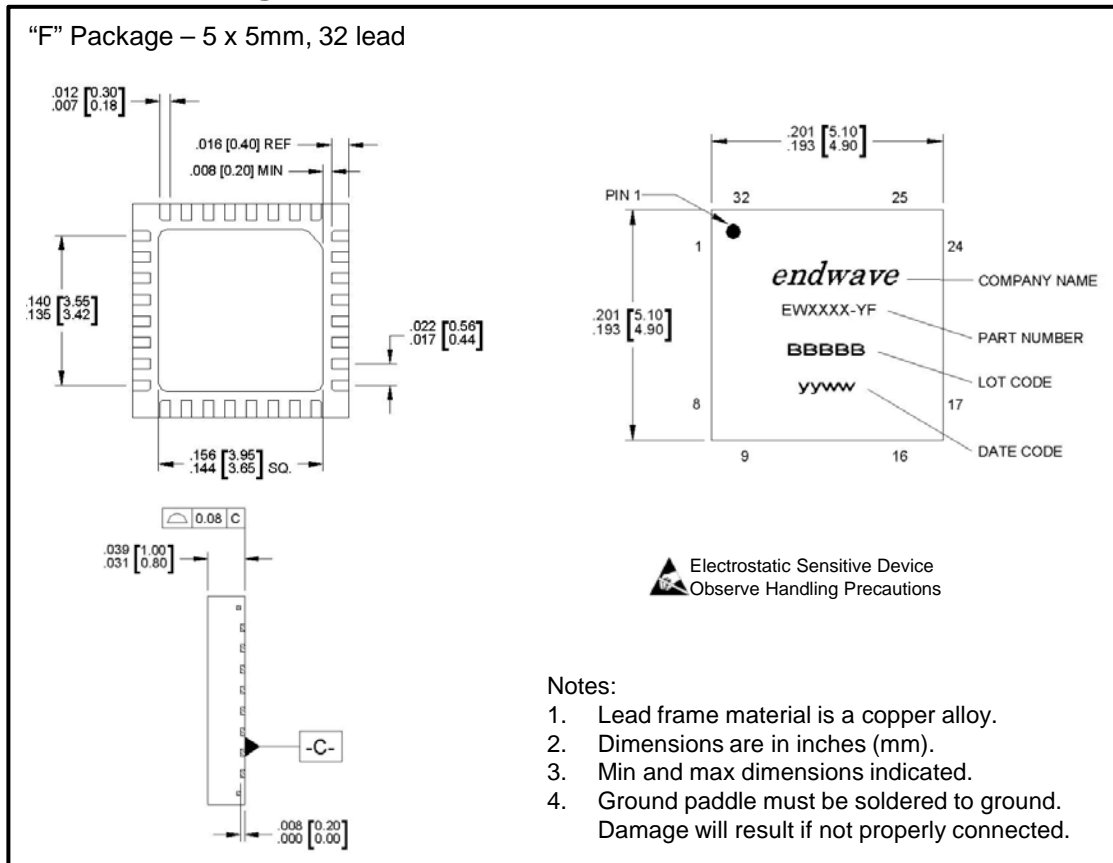
DC & RF Pinout

| Pin Number | Function |
|---|-----------------------|
| 1-5, 15, 16, 20, 21, 23, 24, 30, 31, 32 | No Connection |
| 6, 8, 17, 19, 25, 27, 29 | Ground |
| 7 | RF Output |
| 9 | V_{GC1} |
| 10 | V_{GC2} |
| 11 | V_{G4} (Note 2) |
| 12 | V_{D3} (Note 2) |
| 13 | V_{D2} (Note 2) |
| 14 | V_{D1} (Note 2) |
| 18 | LO Input |
| 22 | V_{G3} (mixer bias) |
| 26 | IF Input2 (Note 1) |
| 28 | IF Input1 (Note 1) |

Note 1: DC inputs may be applied to provide LO or image suppression enhancement.

Note 2: Place 100pF bypass chip capacitor as close as possible to the pin.

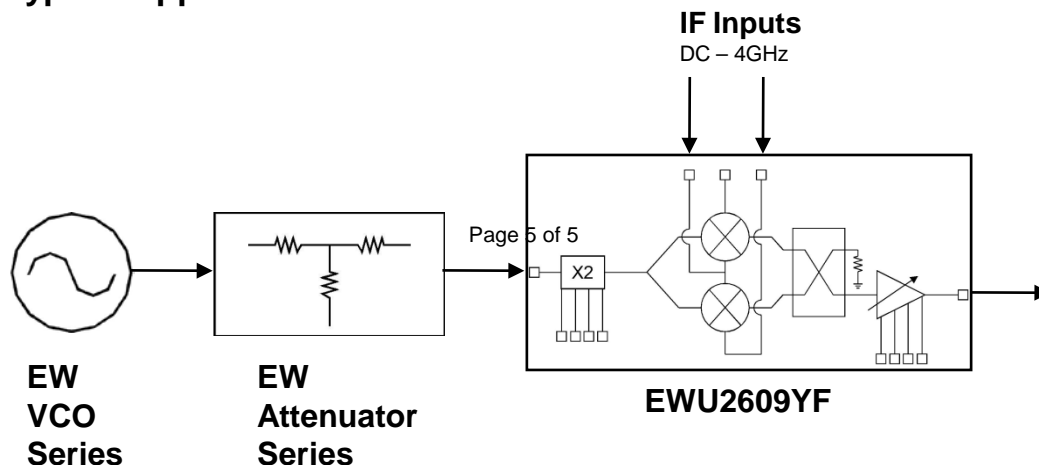
Outline Drawings



Absolute Maximum Ratings

| | |
|----------------------------|---------------|
| IF Input Power | +10 dBm |
| LO Input Power | +15 dBm |
| Supply Voltage (Vd1, 2, 3) | +5.5 V |
| Supply Current (Id total) | 700 mA |
| Storage Temperature | -65 to +150 C |
| Operating Temperature | -40 to +85 C |
| Channel Temperature | 175 C |

Typical Application



Support Documentation

Support documentation including Assembly Notes, Application Notes and Qualification Procedures can be found on our website at www.endwave.com.

Ordering Information

| Part Number | Description |
|--------------|---|
| EWU2609YF | RoHS compliant, 5 x 5mm, 32 lead, QFN "F" package |
| EWU2609YF-EV | EWU2609YF on an Evaluation Board |